

# 2SD1511

## Silicon NPN epitaxial planar type darlington

For low-frequency output amplification

### ■ Features

- Forward current transfer ratio  $h_{FE}$  is designed high, which is appropriate to the driver circuit of motors and printer hammer:  $h_{FE} = 4000$  to 20000.
- A shunt resistor is omitted from the driver.
- Mini power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	100	V
Collector-emitter voltage (Base open)	$V_{CEO}$	80	V
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
Collector current	$I_C$	1	A
Peak collector current	$I_{CP}$	1.5	A
Collector power dissipation *	$P_C$	1	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

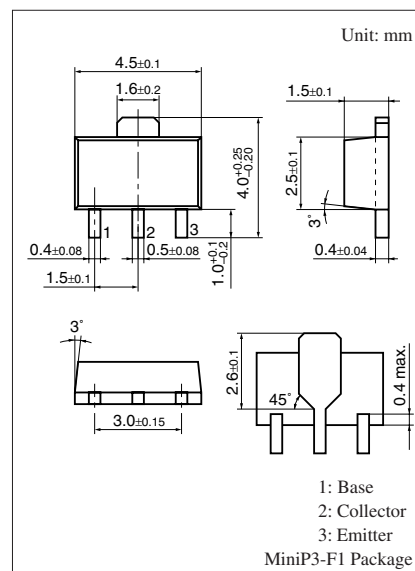
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 100 \mu\text{A}$ , $I_E = 0$	100			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1 \text{ mA}$ , $I_B = 0$	80			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 100 \mu\text{A}$ , $I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 25 \text{ V}$ , $I_E = 0$			100	nA
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 4 \text{ V}$ , $I_C = 0$			100	nA
Forward current transfer ratio *1, 2	$h_{FE}$	$V_{CE} = 10 \text{ V}$ , $I_C = 1 \text{ A}$	4000		40000	—
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = 1 \text{ A}$ , $I_B = 1 \text{ mA}$			1.8	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = 1 \text{ A}$ , $I_B = 1 \text{ mA}$			2.2	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}$ , $I_E = -50 \text{ mA}$ , $f = 200 \text{ MHz}$		150		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement

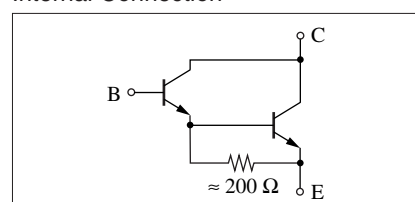
\*2: Rank classification

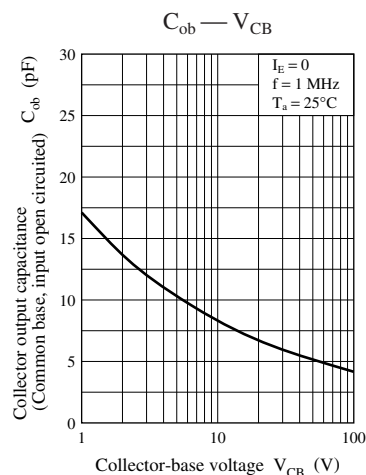
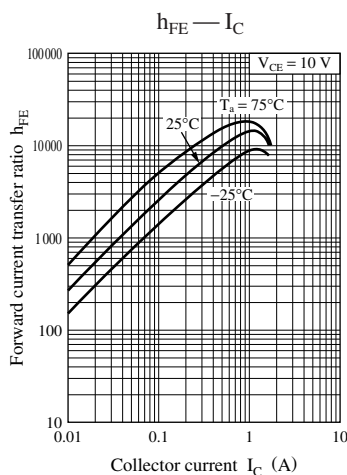
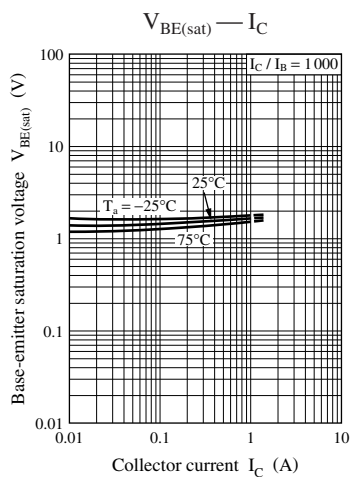
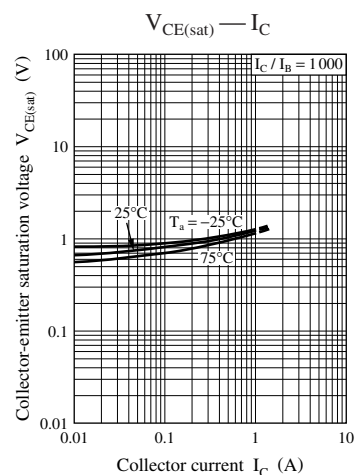
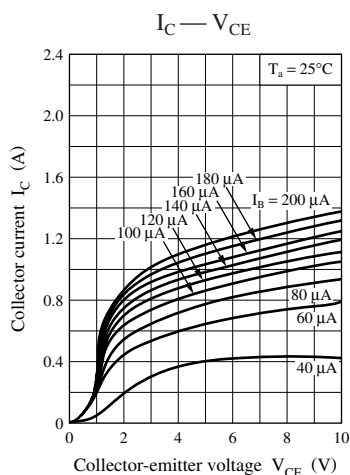
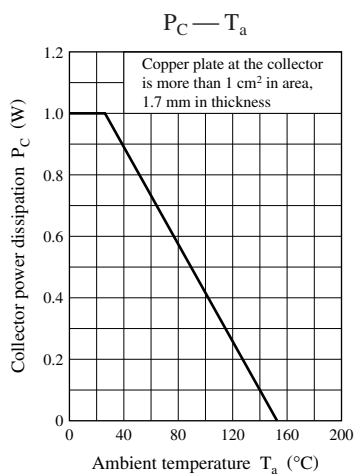
Rank	Q	R	S
$h_{FE}$	4000 to 10000	8000 to 20000	16000 to 40000



Marking Symbol: P

Internal Connection





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